NON-CONDUCTIVE BARRIER FORMATIONS FOR COPPER DAMASCENE TYPE INTERCONNECTS

ABSTRACT

A method for forming dual-damascene type conducting interconnects with non-metallic barriers that protect said interconnects from fluorine out-diffusion from surrounding low-k, fluorinated dielectric materials. One embodiment of the method is particularly suited for forming such interconnects in microelectronics fabrications of the sub 0.15 micron generation.

Fig 7